



## SSC8037GN2

### P-Channel Enhancement Mode MOSFET

#### ➤ Features

VDS	VGS	RDSON Typ.	ID
-30V	±20V	14mR@-10V	-11A
		22mR@-4V5	

#### ➤ Description

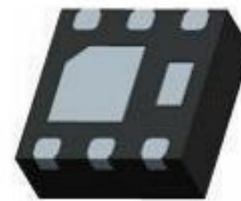
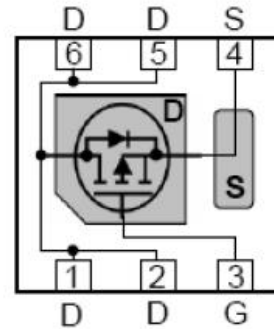
This device is produced with high cell density DMOS trench technology, uses advanced trench technology and design to provide excellent RDSON with low gate charge. This device particularly suits low voltage applications such as portable equipment, power management and other battery powered circuits, and low in-line power dissipation are needed in a very small outline surface mount package.

#### ➤ Applications

- Load Switch
- Portable Devices
- DCDC conversion
- Charging
- Driver for Relay

#### ➤ Pin configuration

Top view



Bottom View



Marking

#### ➤ Ordering Information

Device	Package	Shipping
SSC8037GN2	DFN2x2	3000/Reel



➤ **Absolute Maximum Ratings**( $T_A=25^{\circ}\text{C}$  unless otherwise noted)

<b>Symbol</b>	<b>Parameter</b>	<b>Ratings</b>	<b>Unit</b>
$V_{DSS}$	Drain-to-Source Voltage	-30	V
$V_{GSS}$	Gate-to-Source Voltage	$\pm 20$	V
$I_D$	Continuous Drain Current <sup>a</sup>	-11	A
$I_{DM}$	Pulsed Drain Current <sup>b</sup>	-44	A
$P_D$	Power Dissipation <sup>a</sup>	-2.6	W
$T_J$	Operation junction temperature	-55 to 150	$^{\circ}\text{C}$
$T_{STG}$	Storage temperature range	-55 to 150	$^{\circ}\text{C}$

➤ **Thermal Resistance Ratings**( $T_A=25^{\circ}\text{C}$  unless otherwise noted)

<b>Symbol</b>	<b>Parameter</b>	<b>Ratings</b>	<b>Unit</b>
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance <sup>a</sup>	48	$^{\circ}\text{C}/\text{W}$

Note:

- a. The value of  $R_{\theta JA}$  is measured with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz.copper, in a still air environment with  $T_A=25^{\circ}\text{C}$ . The value in any given application depends on the user is specific board design. The current rating is based on the  $t \leq 10\text{s}$  thermal resistance rating.
- b. Repetitive rating, pulse width limited by junction temperature.

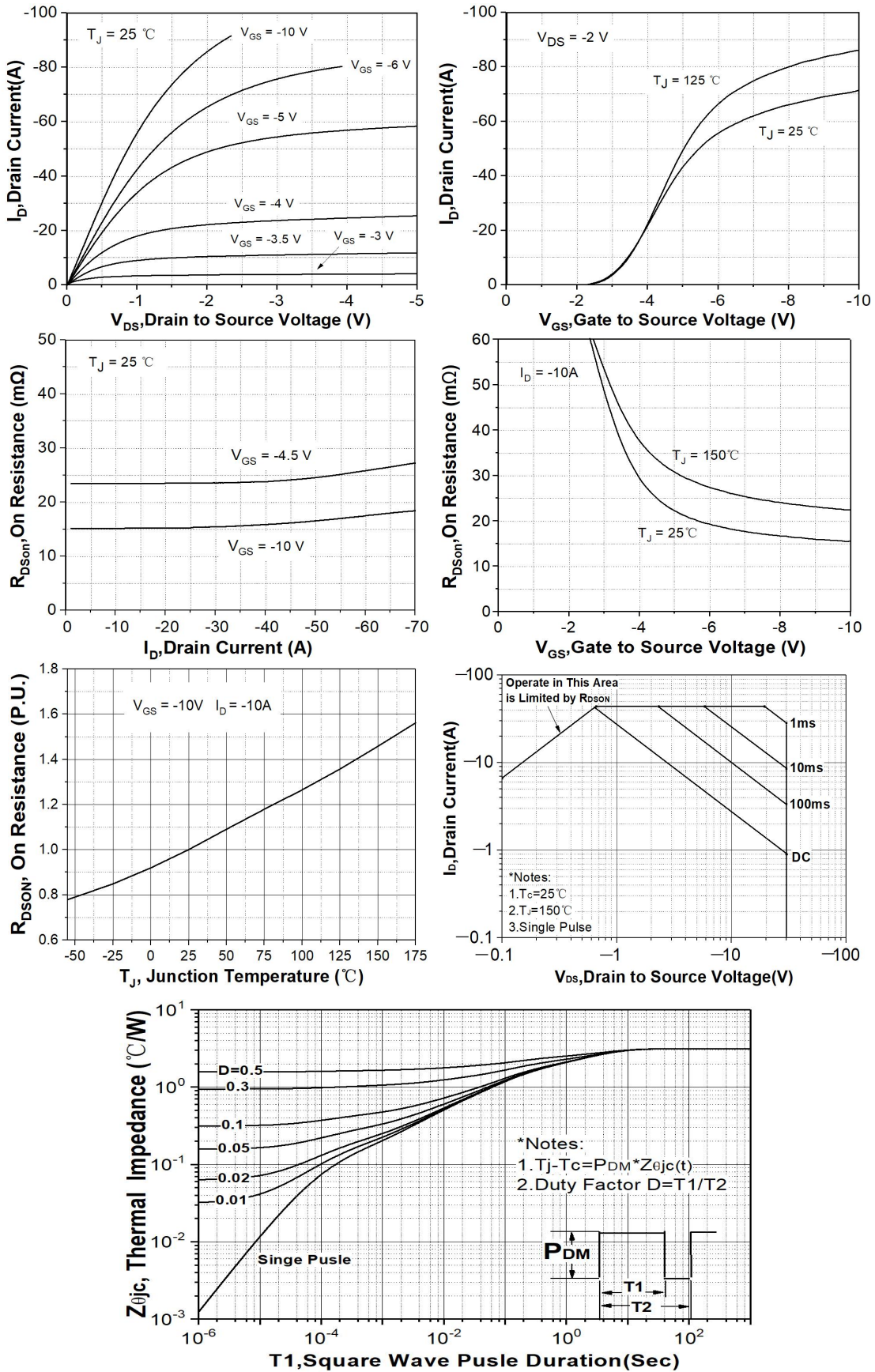


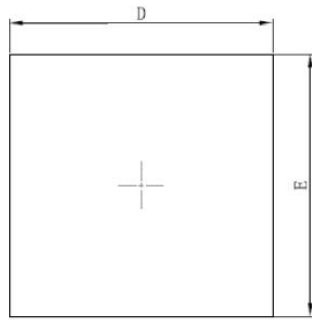
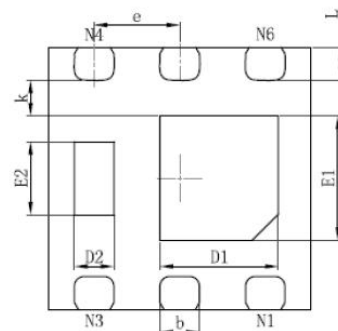
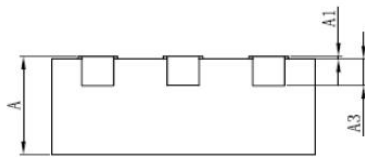
➤ **Electronics Characteristics**( $T_A=25^{\circ}\text{C}$  unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Unit
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-30			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1	-1.8	-3	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=-10V, I_D=-7A$		14	19	mR
		$V_{GS}=-4.5V, I_D=-5A$		22	30	
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=-30V, V_{GS}=0V$			-1	$\mu A$
$I_{GSS}$	Gate-Source leak current	$V_{GS}=\pm 20V, V_{DS}=0V$			$\pm 100$	nA
$V_{SD}$	Forward Voltage	$V_{GS}=0V, I_S=-1A$		-0.85	-1.3	V
$C_{iss}$	Input Capacitance	$V_{DS}=-15V, V_{GS}=0V, f=1MHz$		1300		pF
$C_{oss}$	Output Capacitance			161		
$C_{rss}$	Reverse Transfer Capacitance			183		
$Q_G$	Total Gate charge	$V_{GS}=-10V, V_{DS}=-15V, I_D=-10A$		25.5		nC
$Q_{GS}$	Gate to Source charge			4.3		
$Q_{GD}$	Gate to Drain charge			6.1		
$T_{D(ON)}$	Turn-on delay time	$V_{GS}=-10V, V_{DS}=-15V, R_L=1R, R_G=3R$		8		ns
$T_r$	Rise time			33.5		
$T_{D(OFF)}$	Turn-off delay time			48		
$T_f$	Fall time			11		
$T_{rr}$	Diode Recovery Time	$I_F=-10A, di/dt=200A/\mu s$		23		ns
$Q_{rr}$	Diode Recovery Charge			8		nC



Typical Characteristics ( $T_A=25^\circ\text{C}$  unless otherwise noted)



**➤ Package Information**

**TOP VIEW**

**BOTTOM VIEW**

**SIDE VIEW**
**DFN2x2-6L**

Symbol	Dimensions In Millimeters	
	Min.	Max.
A	0.700	0.800
A1	0.000	0.050
A3	0.203REF.	
D	1.924	2.076
E	1.924	2.076
D1	0.800	1.000
E1	0.850	1.050
D2	0.200	0.400
E2	0.460	0.660
k	0.200MIN.	
b	0.250	0.350
e	0.650TYP.	
L	0.174	0.326



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